

Depletion-Mode Power MOSFET

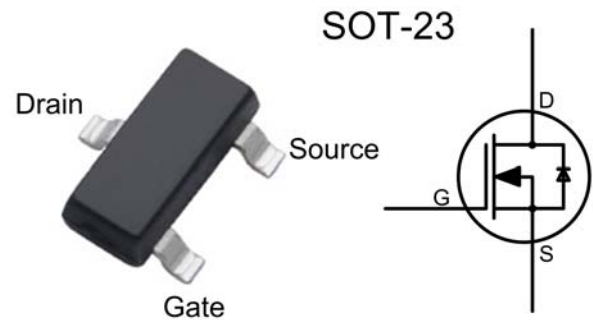
General Features

- ESD improved Capability
- Depletion Mode (Normally On)
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- RoHS Compliant
- Halogen-free available

BV_{DSX}	$R_{DS(ON)} (Max.)$	$I_{DSS,min}$
600V	120 Ω	100mA

Applications

- Normally-on Switches
- SMPS Start-up Circuit
- Linear Amplifier
- Converters
- Constant Current Source
- Telecom



Ordering Information

Part Number	Package	Marking	Remark
HM1060E	SOT-23	61***	Halogen Free

Absolute Maximum Ratings

$T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	HM1060E	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	600	V
V_{DGX}	Drain-to-Gate Voltage ^[1]	600	V
I_D	Continuous Drain Current	0.1	A
I_{DM}	Pulsed Drain Current ^[2]	0.4	
P_D	Power Dissipation	0.50	W
V_{GS}	Gate-to-Source Voltage	± 20	V
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}\text{C}$
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	HM1060E	Unit
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W

Electrical Characteristics

OFF Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSX}	Drain-to-Source Breakdown Voltage	600	--	--	V	$V_{GS} = -5V, I_D = 250\mu A$
$I_{D(OFF)}$	Drain-to-Source Leakage Current	--	--	0.1	μA	$V_{DS} = 600V, V_{GS} = -5V$
		--	--	10	μA	$V_{DS} = 600V, V_{GS} = -5V$ $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	20	μA	$V_{GS} = +20V, V_{DS} = 0V$
		--	--	20		$V_{GS} = -20V, V_{DS} = 0V$

ON Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
I_{DSS}	Saturated Drain-to-Source Current	100	--	130	mA	$V_{GS} = 0V, V_{DS} = 25V$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	110	120	Ω	$V_{GS} = 0V, I_D = 50mA$ [3]
$V_{GS(OFF)}$	Gate-to-Source Cut-off Voltage	-3.0	--	-1.8	V	$V_{DS} = 3V, I_D = 8\mu A$
gfs	Forward Transconductance	--	--	--	mS	$V_{DS} = 10V, I_D = 5mA$

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{ISS}	Input Capacitance	--	--	--	pF	$V_{GS} = -5V$ $V_{DS} = 25V$ $f = 1.0MHz$
C_{OSS}	Output Capacitance	--	--	--		
C_{RSS}	Reverse Transfer Capacitance	--	--	--		
Q_G	Total Gate Charge	--	--	--	nC	$V_{GS} = -5V \sim 5V$ $V_{DS} = 300V, I_D = 7mA$
Q_{GS}	Gate-to-Source Charge	--	--	--		
Q_{GD}	Gate-to-Drain (Miller) Charge	--	--	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	--	--	ns	$V_{GS} = -5V \sim 5V$ $V_{DD} = 300V, I_D = 7mA$ $R_G = 200\Omega$
t_{rise}	Rise Time	--	--	--		
$t_{d(OFF)}$	Turn-off Delay Time	--	--	--		
t_{fall}	Fall Time	--	--	--		

Source-Drain Diode Characteristics

T_A=25°C unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Units	Test Conditions
V _{SD}	Diode Forward Voltage	--	--	1.2	V	I _{SD} =100 mA, V _{GS} = -10 V

NOTE:

[1] T_J=+25°C to +150°C

[2] Repetitive rating, pulse width limited by maximum junction temperature.

[3] Pulse width≤380μs;duty cycle≤2%.

Package Dimensions

SOT-23

